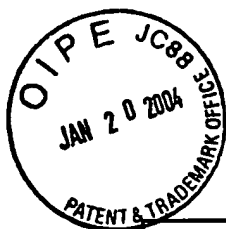


SHEET 1 OF 1

<b>FORM PTO - 1449</b>				<b>ATTORNEY DOCKET NO.: ASC-058B</b>					
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANTS:</b> Leitz <i>et al.</i>					
				<b>SERIAL NO.:</b> 10/646,353					
				<b>FILING DATE:</b> August 22, 2003					
				<b>GROUP:</b> 2826					
<b>U.S. PATENT DOCUMENTS</b>									
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>NAME</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE IF APPROPRIATE</b>		
<b>FOREIGN PATENT DOCUMENTS</b>									
<b>EXAM. INIT.</b>		<b>DOCUMENT NUMBER</b>	<b>DATE</b>	<b>COUNTRY CODE</b>	<b>CLASS</b>	<b>SUB CLASS</b>	<b>FILING DATE</b>	<b>ABSTRACT ONLY</b>	<b>ENGLISH LANG (Y/N)</b>
72	B52	02/13262	02/14/2002	WO				N	Y
↓	B53	03/105189	12/18/2003	WO				N	Y
↓	B54	0 353 423	02/07/1990	EP				N	Y
72	B55	1 014 431	06/28/2000	EP				Y	N
<b>OTHER ART, JOURNAL ARTICLES, ETC.</b>									
<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>								
72	C136	International Search Report for International Patent Application No. PCT/US03/26467, dated July 13, 2004, 3 pages.							
72	C137	Luo <i>et al.</i> , "Compliant effect of low-temperature Si buffer for SiGe growth," <u>Applied Physics Letters</u> , 78(4):454-456 (2001).							
72	C138	Vyatkin <i>et al.</i> , "Study of Strain Relaxation in Epitaxial Structure $\text{Ge}_{0.2}\text{Si}_{0.8}/\text{Si}$ At Thermo-Implantation Treatment by Ion Beam Channeling," <u>Mat. Res. Soc. Symp. Proc.</u> , 585:183-189 (2000).							
<b>EXAMINER</b>		Kevin Quinto			<b>DATE CONSIDERED</b>		7/5/07		

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SHEET 1 OF 1

FORM PTO - 1449  SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT	ATTORNEY DOCKET NO.: ASC-058B  APPLICANTS: Leitz <i>et al.</i>  SERIAL NO.: 10/646,353  FILING DATE: August 22, 2003  GROUP: 2811 2824
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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
72	A176	5,387,796	02/07/1995	Joshi <i>et al.</i>			
72	A177	5,434,102	07/18/1995	Watanabe <i>et al.</i>			

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
72	B49	2-210816	08/22/1990	JP				N	Abstract
72	B50	3-36717	02/18/1991	JP				N	Abstract
72	B51	61-14116	06/28/1986	JP				N	Abstract

## OTHER ART, JOURNAL ARTICLES, ETC.

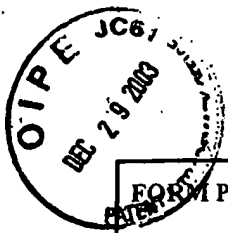
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
72	C132	Feichtinger <i>et al.</i> , "Misfit Dislocation Nucleation Study in p/p+ Silicon," <u>Journal of the Electrochemical Society</u> , 148 (7) (2001), pp. G379-G382.
	C133	Grillot <i>et al.</i> , "Acceptor diffusion and segregation in (Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>0.5</sub> In <sub>0.5</sub> P heterostructures," <u>Journal of Applied Physics</u> , Vol. 91, No. 8 (April 15, 2002), pp. 4891-4899.
	C134	Hsu <i>et al.</i> , "Surface morphology of related GexSi <sub>1-x</sub> films," <u>Applied Physics Letters</u> , 61 (11) (September 14, 1992), pp. 1293-1295.
72	C135	"How to Make Silicon," Wacker University, <a href="http://www.wafernet.com/PresWK/h-ptl-as3_wsc_siltronic_com_pages_training_pages_Silic...">http://www.wafernet.com/PresWK/h-ptl-as3_wsc_siltronic_com_pages_training_pages_Silic...</a> , August 28, 2002.

EXAMINER	Kevin Dwyer	DATE CONSIDERED	2/5/07
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FORM PTO - 1449				ATTORNEY DOCKET NO.: ASC-058B			
INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Leitz <i>et al.</i>			
				SERIAL NO.: 10/646,353			
				FILING DATE: August 22, 2003 GROUP: 2826/2811			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
FL	A1	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A2	2001/0014570	08/16/2001	Wenski <i>et al.</i>			
	A3	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A4	2002/0052084	05/02/2002	Fitzgerald			
	A5	2002/0084000	07/04/2002	Fitzgerald			
	A6	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A7	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A8	2002/0123167	09/05/2002	Fitzgerald			
	A9	2002/0123183	09/05/2002	Fitzgerald			
	A10	2002/0123197	09/05/2002	Fitzgerald <i>et al.</i>			
	A11	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A12	2002/0125497	09/12/2002	Fitzgerald			
	A13	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A14	2002/0185686	12/12/2002	Christiansen <i>et al.</i>			
	A15	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A16	2003/0013323	01/16/2003	Hammond <i>et al.</i>			
	A17	2003/0025131	02/06/2003	Lee <i>et al.</i>			
	A18	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A19	2003/0041798	03/06/2003	Wenski <i>et al.</i>			
	A20	2003/0057439	03/27/2003	Fitzgerald			
	A21	2003/0077867	04/24/2003	Fitzgerald			
	A22	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A23	2003/0127646	07/10/2003	Christiansen <i>et al.</i>			
	A24	2003/0186073	10/02/2003	Fitzgerald			03/18/2003
FL	A25	4,010,045	03/01/1977	Ruehrwein			
EXAMINER Kevin Quindt				DATE CONSIDERED 2/5/07			



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U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
79	A26	4,710,788	12/01/1987	Dambkes <i>et al.</i>			
	A27	4,900,372	12/13/1990	Lee <i>et al.</i>			
	A28	4,987,462	01/22/1991	Kim <i>et al.</i>			
	A29	4,990,979	02/05/1991	Otto			
	A30	4,997,776	03/05/1991	Haramé <i>et al.</i>			
	A31	5,013,681	05/07/1991	Godbey <i>et al.</i>			
	A32	5,091,767	02/25/1992	Bean <i>et al.</i>			
	A33	5,097,630	03/24/1992	Maeda <i>et al.</i>			
	A34	5,155,571	10/13/1992	Wang <i>et al.</i>			
	A35	5,159,413	10/27/1992	Calviello <i>et al.</i>			
	A36	5,166,084	11/24/1992	Pfiester			
	A37	5,177,583	01/05/1993	Endo <i>et al.</i>			
	A38	5,202,284	04/13/1993	Kamins <i>et al.</i>			
	A39	5,207,864	05/04/1993	Bhat <i>et al.</i>			
	A40	5,208,182	05/04/1993	Narayan <i>et al.</i>			
	A41	5,210,052	05/11/1993	Takasaki			
	A42	5,212,110	05/18/1993	Pfiester <i>et al.</i>			
	A43	5,221,413	06/22/1993	Brasen <i>et al.</i>			
	A44	5,241,197	08/31/1993	Murakami <i>et al.</i>			
	A45	5,250,445	10/05/1993	Bean <i>et al.</i>			
	A46	5,252,173	10/12/1993	Inoue			
A47	5,279,687	01/18/1994	Tuppen <i>et al.</i>				
A48	5,285,086	02/08/1994	Fitzgerald				
A49	5,291,439	03/01/1994	Kauffmann <i>et al.</i>				
✓	A50	5,298,452	03/29/1994	Meyerson			
79	A51	5,308,444	05/03/1994	Fitzgerald <i>et al.</i>			
EXAMINER Kevin Quimb				DATE CONSIDERED 2/5/07			



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				FILING DATE: August 22, 2003 GROUP: 2826/2811			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
92	A52	5,310,451	05/10/1994	Tejwani <i>et al.</i>			
	A53	5,316,958	05/31/1994	Meyerson			
	A54	5,346,848	09/13/1994	Gruppen- Shemansky <i>et al.</i>			
	A55	5,374,564	12/20/1994	Bruel			
	A56	5,399,522	03/21/1995	Ohuri			
	A57	5,413,679	05/09/1995	Godbey			
	A58	5,424,243	06/13/1995	Takasaki			
	A59	5,425,846	06/20/1995	Koze <i>et al.</i>			
	A60	5,426,069	06/20/1995	Selvakumar <i>et al.</i>			
	A61	5,426,316	06/20/1995	Mohammad			
	A62	5,442,205	08/15/1995	Brasen <i>et al.</i>			
	A63	5,461,243	10/24/1995	Ek <i>et al.</i>			
	A64	5,461,250	10/24/1995	Burghartz <i>et al.</i>			
	A65	5,462,883	10/31/1995	Dennard <i>et al.</i>			
	A66	5,476,813	12/19/1995	Naruse			
	A67	5,479,033	12/26/1995	Baca <i>et al.</i>			
	A68	5,484,664	01/16/1996	Kitahara <i>et al.</i>			
	A69	5,523,243	06/04/1996	Mohammad			
	A70	5,523,592	06/04/1996	Nakagawa <i>et al.</i>			
	A71	5,534,713	07/09/1996	Ismail <i>et al.</i>			
	A72	5,536,361	07/16/1996	Kondo <i>et al.</i>			
	A73	5,540,785	07/30/1996	Dennard <i>et al.</i>			
	A74	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A75	5,617,351	04/01/1997	Bertin <i>et al.</i>			
	A76	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A77	5,633,516	05/27/1997	Mishima <i>et al.</i>			
KL	A78	5,659,187	08/19/1997	Legoues <i>et al.</i>			
EXAMINER Kevin Qumto				DATE CONSIDERED 2/5/07			



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INFORMATION DISCLOSURE STATEMENT				APPLICANT(S): Leitz <i>et al.</i>			
				SERIAL NO.: 10/646,353			
				FILING DATE: August 22, 2003 GROUP: 2811 <span style="float: right;">2826</span>			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
78	A79	5,683,934	11/04/1997	Candelaria			
	A80	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A81	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A82	5,728,623	03/17/1998	Mori			
	A83	5,739,567	04/14/1998	Wong			
	A84	5,759,898	06/02/1998	Ek <i>et al.</i>			
	A85	5,777,347	07/07/1998	Bartelink			
	A86	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A87	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A88	5,792,679	08/11/1998	Nakato			
	A89	5,801,085	09/01/1998	Kim <i>et al.</i>			
	A90	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A91	5,810,924	09/22/1998	Legoues <i>et al.</i>			
	A92	5,828,114	10/27/1998	Kim <i>et al.</i>			
	A93	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A94	5,859,864	01/12/1999	Jewell			
	A95	5,877,070	03/02/1999	Goesele <i>et al.</i>			
A96	5,891,769	04/06/1999	Liaw <i>et al.</i>				
A97	5,906,708	05/25/1999	Robinson <i>et al.</i>				
A98	5,906,951	05/25/1999	Chu <i>et al.</i>				
A99	5,912,479	06/15/1999	Mori <i>et al.</i>				
A100	5,943,560	08/24/1999	Chang <i>et al.</i>				
A101	5,963,817	10/05/1999	Chu <i>et al.</i>				
A102	5,966,622	10/12/1999	Levine <i>et al.</i>				
A103	5,998,807	12/07/1999	Lustig <i>et al.</i>				
A104	6,010,937	01/04/2000	Karam <i>et al.</i>				
A105	6,013,134	01/11/2000	Chu <i>et al.</i>				
77	A106	6,030,884	02/29/2000	Mori			
	A107	6,033,974	03/07/2000	Henley <i>et al.</i>			
EXAMINER <i>Kevin Quinto</i>				DATE CONSIDERED <i>2/5/07</i>			



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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
77	A108	6,033,995	03/07/2000	Muller			
	A109	6,039,803	03/21/2000	Fitzgerald <i>et al.</i>			
	A110	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
	A111	6,059,895	05/09/2000	Chu <i>et al.</i>			
	A112	6,074,919	06/13/2000	Gardner <i>et al.</i>			
	A113	6,096,590	08/01/2000	Chan <i>et al.</i>			
	A114	6,103,559	08/15/2000	Gardner <i>et al.</i>			
	A115	6,107,653	08/22/2000	Fitzgerald			
	A116	6,111,267	08/29/2000	Fischer <i>et al.</i>			
	A117	6,117,750	09/12/2000	Bensahel <i>et al.</i>			
	A118	6,124,614	09/26/2000	Ryum <i>et al.</i>			
	A119	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A120	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A121	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A122	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A123	6,153,495	11/28/2000	Kub <i>et al.</i>			
	A124	6,154,475	11/28/2000	Soref <i>et al.</i>			
	A125	6,160,303	12/12/2000	Fattaruso			
	A126	6,162,688	12/19/2000	Gardner <i>et al.</i>			
	A127	6,184,111	02/06/2001	Henley <i>et al.</i>			
	A128	6,191,006	02/20/2001	Mori			
	A129	6,191,007	02/20/2001	Matsui <i>et al.</i>			
	A130	6,191,432	02/20/2001	Sugiyama <i>et al.</i>			
	A131	6,194,722	02/27/2001	Fiorini <i>et al.</i>			
	A132	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A133	6,207,977	03/27/2001	Augusto			
	A134	6,210,988	04/03/2001	Howe <i>et al.</i>			
	A135	6,218,677	04/17/2001	Broekaert			
77	A136	6,232,138	05/15/2001	Fitzgerald <i>et al.</i>			
77	A137	6,235,567	05/22/2001	Huang			
EXAMINER Kervh Quinto				DATE CONSIDERED 2/5/07			



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ATTORNEY DOCKET NO.: ASC-058B

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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
99	A138	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A139	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A140	6,251,755	06/26/2001	Furukawa <i>et al.</i>			
	A141	6,261,929	07/17/2001	Gehrke <i>et al.</i>			
	A142	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A143	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A144	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A145	6,291,321	09/18/2001	Fitzgerald			
	A146	6,313,016	11/06/2001	Kibbel <i>et al.</i>			
	A147	6,316,301	11/13/2001	Kant			
	A148	6,323,108	11/27/2001	Kub <i>et al.</i>			
	A149	6,329,063	12/11/2001	Lo <i>et al.</i>			
	A150	6,335,546	01/01/2002	Tsuda <i>et al.</i>			
	A151	6,339,232	01/15/2002	Takagi			
	A152	6,350,993	02/26/2002	Chu <i>et al.</i>			
	A153	6,368,733	04/09/2002	Nishinaga			
	A154	6,372,356	04/16/2002	Thornton <i>et al.</i>			
	A155	6,399,970	06/04/2002	Kubo <i>et al.</i>			
	A156	6,403,975	06/11/2002	Brunner <i>et al.</i>			
	A157	6,406,589	06/18/2002	Yanagisawa			
	A158	6,407,406	06/18/2002	Tezuka			
	A159	6,420,937	07/16/2002	Akatsuka <i>et al.</i>			
	A160	6,425,951	07/30/2002	Chu <i>et al.</i>			
	A161	6,429,061	08/06/2002	Rim			
	A162	6,482,749	11/19/2002	Billington <i>et al.</i>			
	A163	6,503,773	01/07/2003	Fitzgerald			
✓	A164	6,515,335	02/04/2003	Christiansen <i>et al.</i>			
99	A165	6,518,644	02/11/2003	Fitzgerald			
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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
72	A166	6,521,041	02/18/2003	Wu <i>et al.</i>			
	A167	6,525,338	02/25/2003	Mizushima <i>et al.</i>			
	A168	6,555,839	04/29/2003	Fitzgerald			
	A169	6,573,126	06/03/2003	Cheng <i>et al.</i>			
	A170	6,576,532	06/10/2003	Jones <i>et al.</i>			
	A171	6,583,015	06/24/2003	Fitzgerald <i>et al.</i>			
	A172	6,593,191	07/15/2003	Fitzgerald			
	A173	6,594,293	07/15/2003	Bulsara <i>et al.</i>			
✓	A174	6,602,613	08/05/2003	Fitzgerald			
72	A175	6,603,156	08/05/2003	Rim			

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
72	B1	41 01 167	07/23/1992	DE				N	Abstract
	B2	0 514 018	11/19/1992	EP				N	Y
	B3	0 587 520	03/16/1994	EP				N	Y
	B4	0 683 522	11/22/1995	EP				N	Y
	B5	0 828 296	03/11/1998	EP				N	Y
	B6	0 829 908	03/18/1998	EP				N	Y
	B7	0 838 858	04/29/1998	EP				N	Abstract
	B8	1 020 900	07/19/2000	EP				N	Y
	B9	1 174 928	01/23/2002	EP				N	Y
✓	B10	2 342 777	04/19/2000	GB				Y	Y
72	B11	4-307974	10/30/1992	JP				N	Abstract

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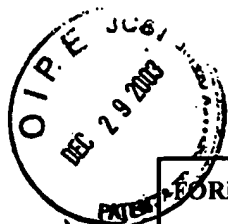
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FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
79	B12	5-166724	07/02/1993	JP				N	Abstract
	B13	6-177046	06/24/1994	JP				N	Abstract
	B14	6-244112	09/02/1994	JP				Y	Y
	B15	6-252046	09/09/1994	JP				Y	Y
	B16	7-94420	04/07/1995	JP				N	Abstract
	B17	7-106446	04/21/1995	JP				N	Abstract
	B18	7-240372	09/12/1995	JP				N	Abstract
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79	B36	01/54175	07/26/2001	WO				N	Y
EXAMINER				Ken Quanta		DATE CONSIDERED 2/5/07			



FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT					ATTORNEY DOCKET NO.: ASC-058B APPLICANT(S): Leitz <i>et al.</i> SERIAL NO.: 10/646,353 FILING DATE: August 22, 2003 GROUP: 28/1				
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
72	B37	01/54202	07/26/2001	WO				N	Y
	B38	01/93338	12/06/2001	WO				N	Y
	B39	01/99169	12/27/2001	WO				N	Y
	B40	02/071488	09/12/2002	WO				N	Y
	B41	02/071491	09/12/2002	WO				N	Y
	B42	02/071495	09/12/2002	WO				N	Y
	B43	02/082514	10/17/2002	WO				N	Y
	B44	02/13262	02/14/2002	WO				N	Y
	B45	02/15244	02/21/2002	WO				N	Y
	B46	02/27783	04/04/2002	WO				N	Y
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OTHER ART, JOURNAL ARTICLES, ETC.									
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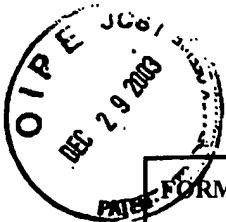


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INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/646,353	2824
		FILING DATE: August 22, 2003	GROUP: 2811
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INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/646,353	
		FILING DATE: August 22, 2003 GROUP: 2826/2911	
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OTHER ART, JOURNAL ARTICLES, ETC.			
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INFORMATION DISCLOSURE STATEMENT		APPLICANT(S): Leitz <i>et al.</i>	
		SERIAL NO.: 10/646,353	2826
		FILING DATE: August 22, 2003	GROUP: 2811
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FORM PTO - 1449

## INFORMATION DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058B

APPLICANT(S): Leitz *et al.*

SERIAL NO.: 10/646,353

FILING DATE: August 22, 2003 GROUP: 2876

## OTHER ART, JOURNAL ARTICLES, ETC.

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OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
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PATENT FORM PTO - 1449 <b>INFORMATION DISCLOSURE STATEMENT</b>		ATTORNEY DOCKET NO.: ASC-058B APPLICANT(S): Leitz <i>et al.</i> SERIAL NO.: 10/646,353 FILING DATE: August 22, 2003 GROUP: 2811	
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